

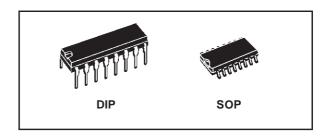


# TRIPLE 2-CHANNEL ANALOG MULTIPLEXER/DEMULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR V<sub>DD</sub> - V<sub>EE</sub> = 15V
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE ± 100pA (Typ.) at V<sub>DD</sub> V<sub>EE</sub> = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at  $f_{IS} = 1$ KHz,  $V_{IS} = 5$   $V_{pp}$ ,  $V_{DD} V_{SS} \ge 10$ V, RL = 10K $\Omega$
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS: 0.2 µW (Typ.) at V<sub>DD</sub> - V<sub>SS</sub> = V<sub>DD</sub> - V<sub>EE</sub> =10V
- MATCHED SWITCH CHARACTERISTICS :  $R_{ON} = 5Ω$  (Typ.) FOR  $V_{DD} V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS: DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I<sub>I</sub> = 100nA (MAX) AT V<sub>DD</sub> = 18V T<sub>A</sub> = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

#### **DESCRIPTION**

The HCF4053B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor



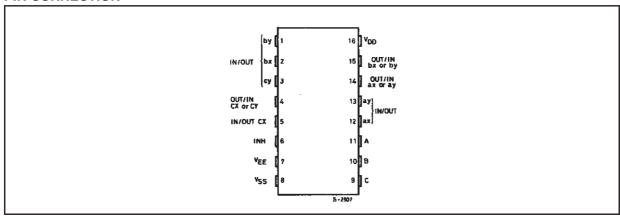
#### **ORDER CODES**

PACKAGE	TUBE	T & R
DIP	HCF4053BEY	
SOP	HCF4053BM1	HCF4053M013TR

technology available in DIP and SOP packages. The HCF4053B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full  $\rm V_{DD}$ -  $\rm V_{SS}$  and  $\rm V_{DD}$ -  $\rm V_{EE}$  supply voltage range, independent of the logic state of the control signals.

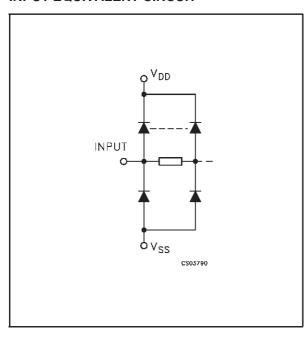
When a logic "1" is present at the inhibit input terminal all channel are off. This device is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a single pole double-throw configuration.

#### **PIN CONNECTION**



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### **INPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

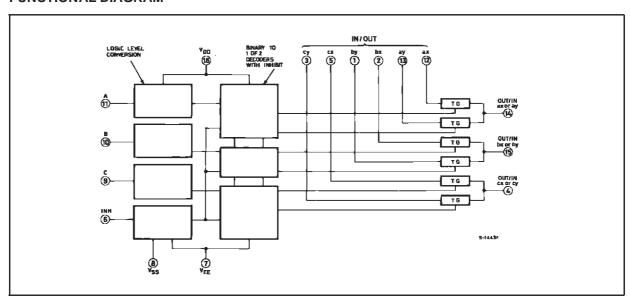
PIN No	SYMBOL	NAME AND FUNCTION
11, 10, 9	A, B, C	Binary Control Inputs
6	INH	Inhibit Inputs
12, 13, 2, 1, 5, 3	IN/OUT	ax,ay,bx,by,cx,cy Input/ Output
14	OUT/IN	ax or ay
15	OUT/IN	bx or by
4	OUT/IN	cx or cy
7	$V_{EE}$	Supply Voltage
8	$V_{SS}$	Negative Supply Voltage
16	$V_{DD}$	Positive Supply Voltage

#### **TRUTH TABLE**

INHIBIT	C or B or A	
0	0	ax or bx or cx
0	1	ay or by or cy
1	X	NONE

X : Don't Care

#### **FUNCTIONAL DIAGRAM**



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	-0.5 to +22	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
l <sub>l</sub>	DC Input Current	± 10	mA
P <sub>D</sub>	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T <sub>op</sub>	Operating Temperature	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage	3 to 20	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

All voltage values are referred to VSS pin voltage. (\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65 °C to 85 °C

#### **DC SPECIFICATIONS**

		T	est Coi	ndition		Value							
Symbol	Parameter	V <sub>IS</sub>		V <sub>SS</sub>	V <sub>DD</sub>	Т	$T_A = 25^{\circ}C$		-40 to 85°C		C -55 to 125°C		Unit
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μА
	switches ON or all switches OFF)				15		0.04	20		600		600	μΑ
	,				20		0.08	100		3000		3000	
SWITCH					_	_							
R <sub>ON</sub>	Resistance	0 <u>&lt;</u> V <sub>I</sub> <u>&lt;</u>			5		470	1050		1200		1200	
		V <sub>DD</sub>	0	0	10		180	400		520		520	Ω
		- 00			15		125	280		360		360	
$\Delta_{ON}$	Resistance $\Delta_{RON}$	0 <u>&lt;</u> V <sub>I</sub> <u>&lt;</u>			5		10						
	(between any 2 of	V <sub>DD</sub>	0	0	10		10						Ω
	4 switches)	DD			15		5						
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA
Cı	Input Capacitance						5						
Co	Output Capacitance		-5	-5	5		9						pF
C <sub>IO</sub>	Feed through	1					0.2						
CONTRO	DL (Address or Inhi	bit)											
V <sub>IL</sub>	Input Low Voltage		Vee :	= V <sub>SS</sub>	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
		= VDD	to \		15			4		4		4	
V <sub>IH</sub>	Input High Voltage	thru 1KΩ		2μΑ	5	3.5			3.5		3.5		
				I OFF	10	7			7		7		V
			chan	nels)	15	11			11		11		
I <sub>IH,</sub> I <sub>IL</sub>	Input Leakage Current	VI	V <sub>I</sub> = 0/18V		18		±10 <sup>-3</sup>	±0.1		±1		±1	μА
C <sub>I</sub>	Input Capacitance						5	7.5					pF

<sup>\*</sup> Determined by minimum feasible leakage measurement for automating testing.

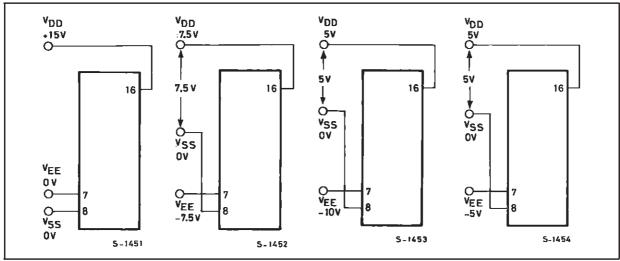
**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}C$ ,  $C_{L} = 50 pF$ , all input square wave rise and fall time = 20 ns )

				Test Co	ndition				Value		Unit
Parameter	V <sub>EE</sub> (V)	<b>R</b> <sub>L</sub> (ΚΩ)	f <sub>I</sub> (KHz)	<b>V</b> <sub>I</sub> (V)	V <sub>SS</sub>	V <sub>DD</sub> (V)		Min.	Тур.	Max.	
Propagation Delay				V		5			30	60	
Time (signal input to		200		V <sub>DD</sub>		10	1		15	30	ns
output)						15	1		11	20	
Frequency Response Channel "ON" (sine wave input) at	= V <sub>SS</sub>	1		5(*)		10	V <sub>O</sub> at Common OUT/IN		25		MHz
20 log V <sub>O</sub> /V <sub>I</sub> = - 3dB							V <sub>O</sub> at any channel		60		
Feed through (all channels OFF) at	V	4		F(*)		40	V <sub>O</sub> at Common OUT/IN		10		N 41 1-
$20 \log V_{O}/V_{I} = -40 dB$	= V <sub>SS</sub>	1		5(*)		10	V <sub>O</sub> at any channel		8		MHz
Frequency Signal Crosstalk at	= V <sub>SS</sub>	1		E/*\		10	Between any 2 Sections (IN pin 2, OUT pin 14)		2.5		MHz
$20 \log V_{O}/V_{I} = -40 dB$	- vss	'		5(*)		10	Between any 2 Sections (IN pin 15, OUT pin 14)		6		IVITIZ
Circa Marra Diatantian				2(*)		5			0.3		
Sine Wave Distortion f <sub>IS</sub> = 1KHz Sine Wave	= V <sub>SS</sub>	10	1	3(*)		10	]		0.2		%
115 - 11412 0110 11410				5(*)		15	]		0.12		
CONTROL (Address	or Inhibi	t)									
Propagation Delay:	0				0	5			360	720	
Address to Signal	0				0	10			160	320	ns
OUT (Channels ON or OFF)	0				0	15			120	240	113
01011)	-5				0	5			225	450	
Propagation Delay:	0				0	5			360	720	
Inhibit to Signal OUT	0	1			0	10			160	320	ns
(Channel turning ON)	0	'			0	15			120	240	113
	-10				0	5			200	400	
Propagation Delay:	0					5			200	450	
Inhibit to Signal OUT	0	10				10			90	210	ns
(Channel turning OFF)	0	] 10				15			70	160	] 115
	-10					5			130	300	
Address or Inhibit to Signal Crosstalk	0	10 <sup>(1)</sup>			0	10	$V_C = V_{DD} - V_{SS}$ (square wave)		65		mV peak

<sup>(1)</sup> Both ends of channel.

\* Peak to Peak voltage symmetrical about (V<sub>DD</sub> - V<sub>EE</sub> ) /2

#### **TYPICAL BIAS VOLTAGES**



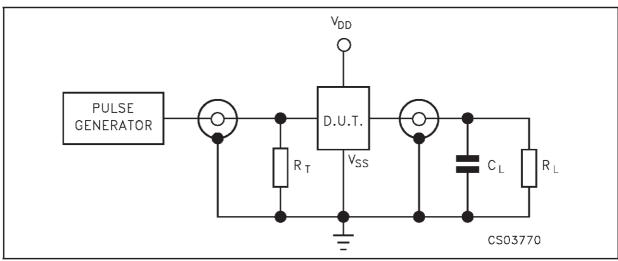
The ADDRESS (digital-control inputs) and INHIBIT logic levels are: "0"=V<sub>SS</sub> and "1"=V<sub>DD</sub>. The analog signal (through the TG) may swing from  $V_{EE}$  to  $V_{DD}$ 

#### **SPECIAL CONSIDERATIONS**

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if  $V_{DD}$  -  $V_{SS}$  = 3V, a  $V_{DD}$  -  $V_{EE}$  of up to 13V can be controlled; for  $V_{DD}$  -  $V_{EE}$  level differences above 13V, a  $V_{DD}$  -  $V_{SS}$  of at least 4.5V is required. For example, if  $V_{DD}$  = +5,  $V_{SS}$  = 0, and  $V_{EE}$  = -13.5, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In

certain applications, the external load resistor current may include both  $\rm V_{\rm DD}$  and signal-line components. To avoid drawing  $\rm V_{\rm DD}$  current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from RON values shown in DC SPECIFICATIONS). No V<sub>DD</sub> current will flow through R<sub>I</sub> if the switch current flows into leads 4, 14 and 15.

#### **TEST CIRCUIT**

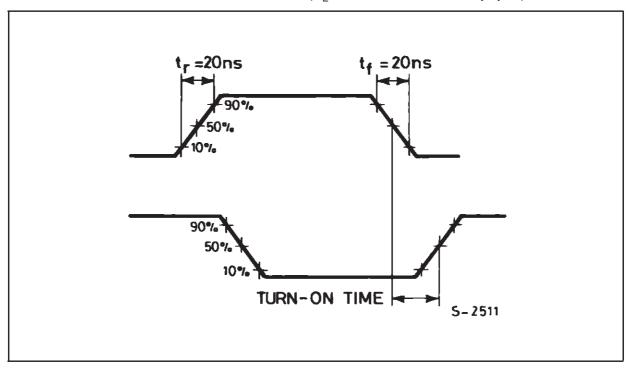


C<sub>L</sub> = 50pF or equivalent (includes jig and probe capacitance)

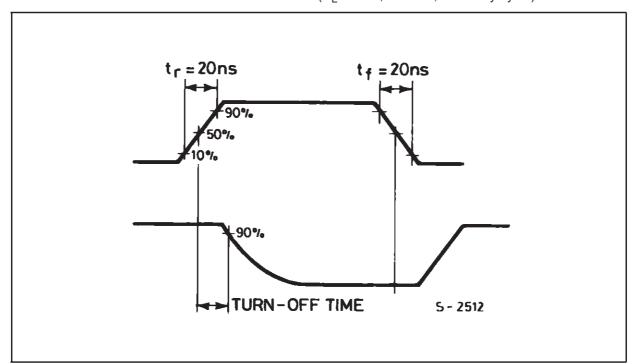
 $R_L = 200 K \Omega$   $R_T = Z_{OUT}$  of pulse generator (typically  $50 \Omega$ )

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**WAVEFORM 1 : CHANNEL BEING TURNED ON** ( $R_L = 1 \text{K}\Omega$ , f=1MHz; 50% duty cycle)



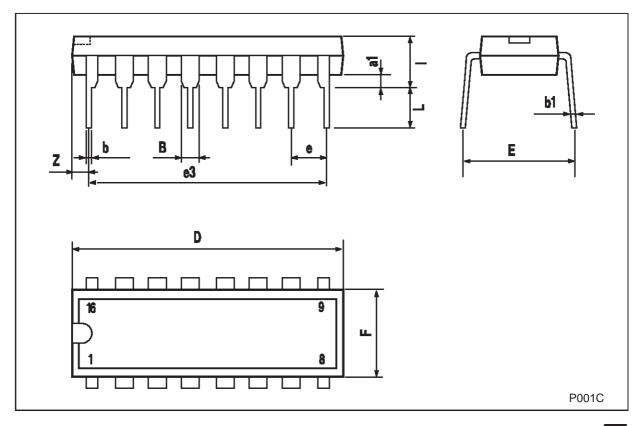
**WAVEFORM 2 : CHANNEL BEING TURNED OFF** ( $R_L$  = 1K $\Omega$ , f=1MHz; 50% duty cycle)



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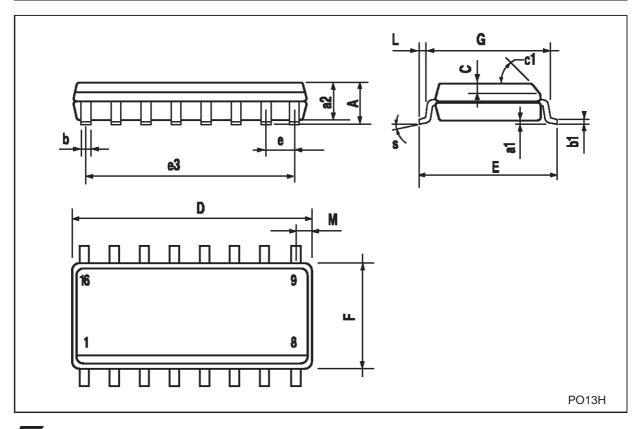
# Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.		mm.				
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



## **SO-16 MECHANICAL DATA**

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)	•			
D	9.8		10	0.385		0.393		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S		•	8° (1	max.)	•			



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